

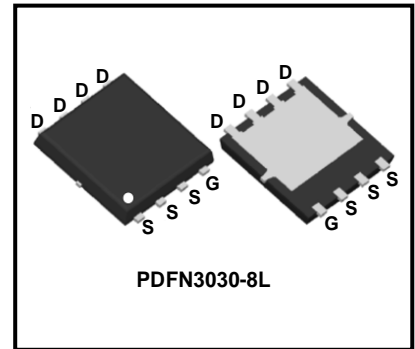
30V N-Channel Enhancement Mode Power MOSFET

Description

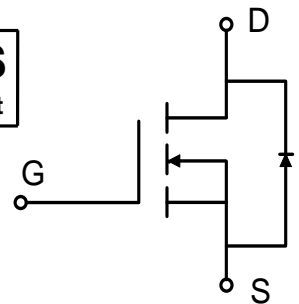
WMQ32N03TS uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Features

- $V_{DS} = 30V$, $I_D = 35A$
 $R_{DS(on)} < 9m\Omega @ V_{GS} = 10V$
 $R_{DS(on)} < 13.5m\Omega @ V_{GS} = 4.5V$
- Green Device Available
- Low Gate Charge
- Advanced High Cell Density Trench Technology
- 100% EAS Guaranteed



RoHS
compliant



Applications

- Power Management Switches
- DC/DC Converter

Absolute Maximum Ratings ($T_A = 25^\circ C$, unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|--------------------|---------------------|------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | $T_C = 25^\circ C$ | 35 |
| | | $T_C = 100^\circ C$ | 22 |
| Pulsed Drain Current ¹ | I_{DM} | 140 | A |
| Single Pulse Avalanche Energy ² | EAS | 49 | mJ |
| Total Power Dissipation | $T_C = 25^\circ C$ | P_D | 18.4 |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ C$ |

Thermal Characteristics

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------|--------------|
| Thermal Resistance from Junction-to-Ambient ³ | $R_{\theta JA}$ | 40 | $^\circ C/W$ |
| Thermal Resistance from Junction-to-Case | $R_{\theta JC}$ | 6.8 | $^\circ C/W$ |

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
|--|-----------------------|--|------|------|------|------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0V, I _D = 250μA | 30 | - | - | V |
| Gate-body Leakage current | I _{GSS} | V _{DS} = 0V, V _{GS} = ±20V | - | - | ±100 | nA |
| Zero Gate Voltage Drain Current | T _J =25°C | V _{DS} = 30V, V _{GS} = 0V | - | - | 1 | μA |
| | T _J =100°C | | - | - | 100 | |
| Gate-Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250μA | 1 | 1.65 | 2 | V |
| Drain-Source On-Resistance ⁴ | R _{DS(on)} | V _{GS} = 10V, I _D = 20A | - | 6.9 | 9 | mΩ |
| | | V _{GS} = 4.5V, I _D = 10A | - | 10 | 13.5 | |
| Forward Transconductance ⁴ | g _{fs} | V _{DS} = 10V, I _D = 20A | - | 62 | - | S |
| Dynamic Characteristics⁵ | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 15V, V _{GS} = 0V, f = 1MHz | - | 995 | - | pF |
| Output Capacitance | C _{oss} | | - | 127 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 115 | - | |
| Gate Resistance | R _g | f = 1MHz | - | 3 | - | Ω |
| Switching Characteristics⁵ | | | | | | |
| Total Gate Charge | Q _g | V _{GS} = 10V, V _{DS} = 15V, I _D = 20A | - | 20 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 4 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 3.7 | - | |
| Turn-On Delay Time | t _{d(on)} | V _{GS} = 10V, V _{DD} = 15V, R _G = 3Ω, I _D = 20A | - | 5.4 | - | ns |
| Rise Time | t _r | | - | 4.8 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 23 | - | |
| Fall Time | t _f | | - | 7.5 | - | |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 20A, dI/dt = 100A/μs | - | 16 | - | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | - | 3.2 | - | nC |
| Drain-Source Body Diode Characteristics | | | | | | |
| Diode Forward Voltage ⁴ | V _{SD} | I _S = 20A, V _{GS} = 0V | - | - | 1.2 | V |
| Continuous Source Current | I _S | T _C = 25°C | - | - | 35 | A |

Note :

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The test condition is V_{DD} = 25V, V_{GS} = 10V, L = 0.5mH, I_{AS} = 14A.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

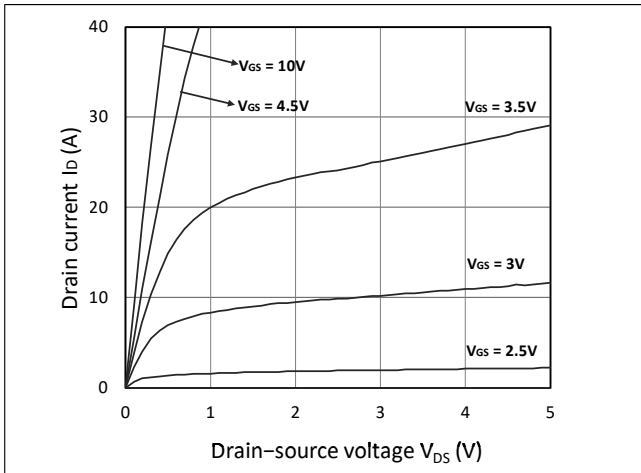


Figure 1. Output Characteristics

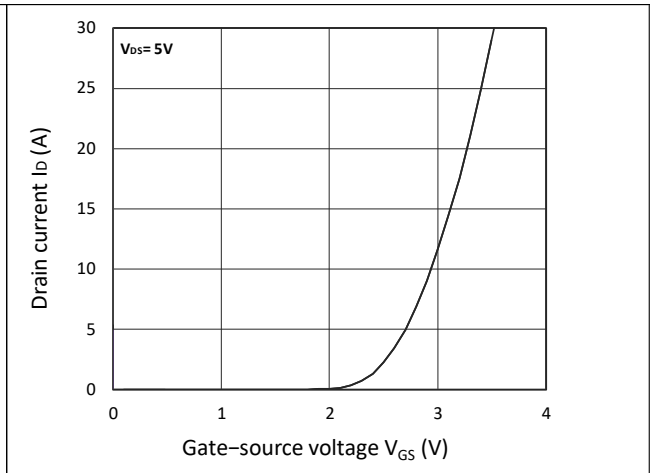


Figure 2. Transfer Characteristics

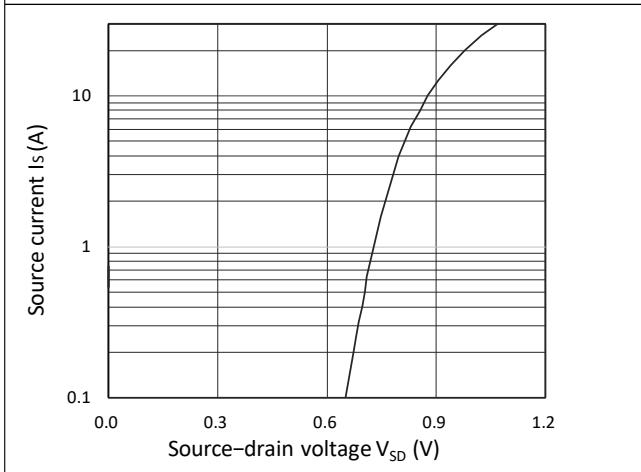


Figure 3. Forward Characteristics of Reverse

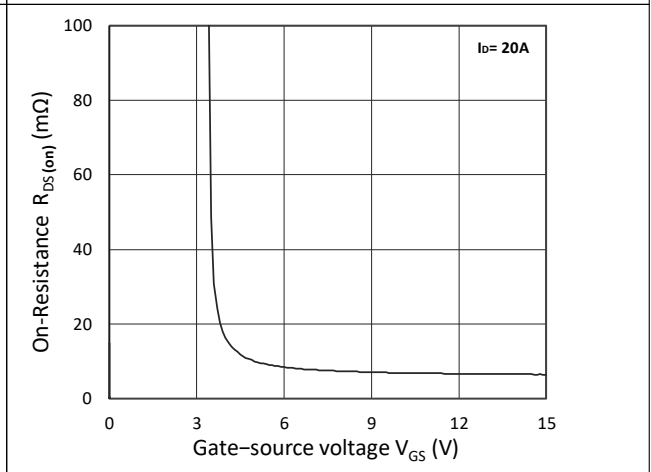


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

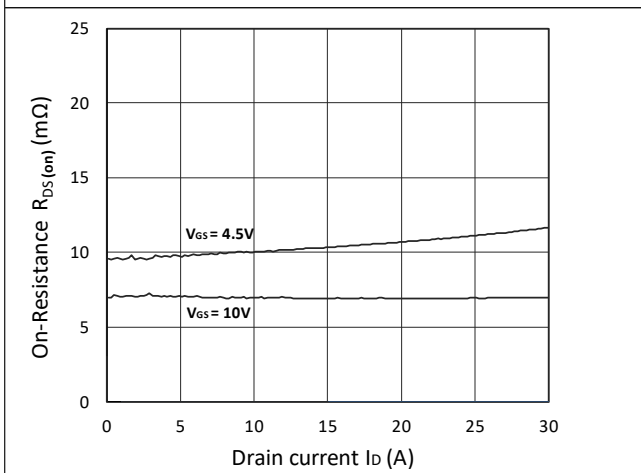


Figure 5. $R_{DS(ON)}$ vs. I_D

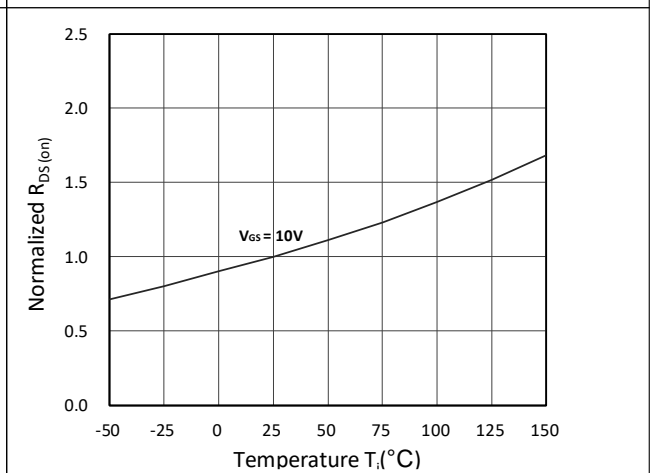


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

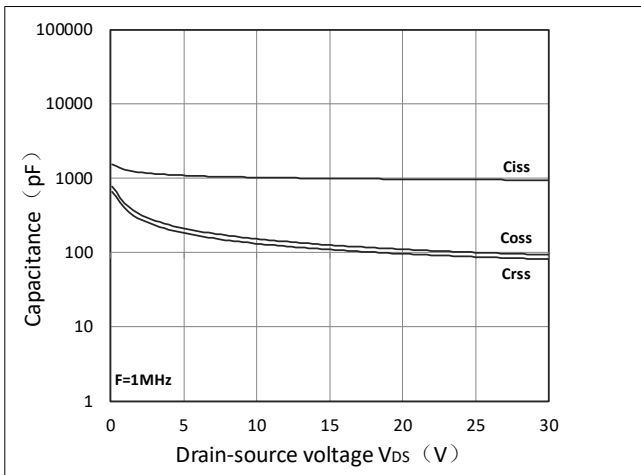


Figure 7. Capacitance Characteristics

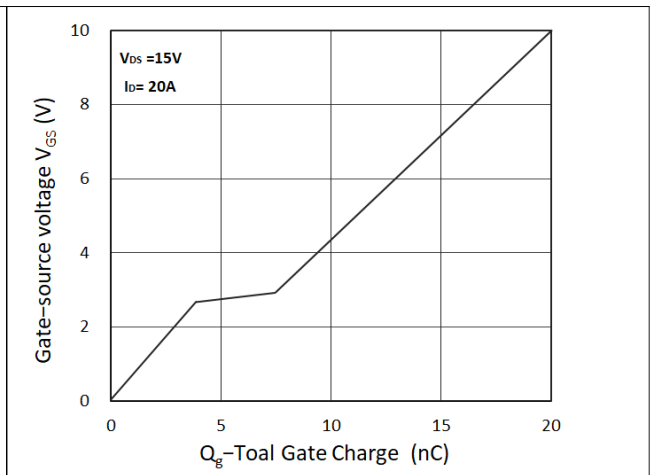


Figure 8. Gate Charge Characteristics

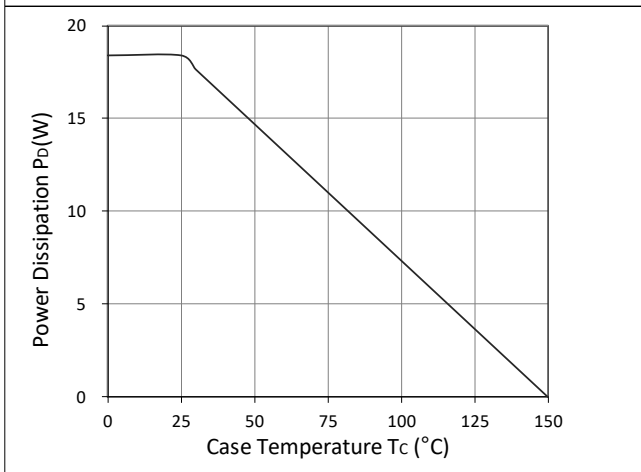


Figure 9. Power Dissipation

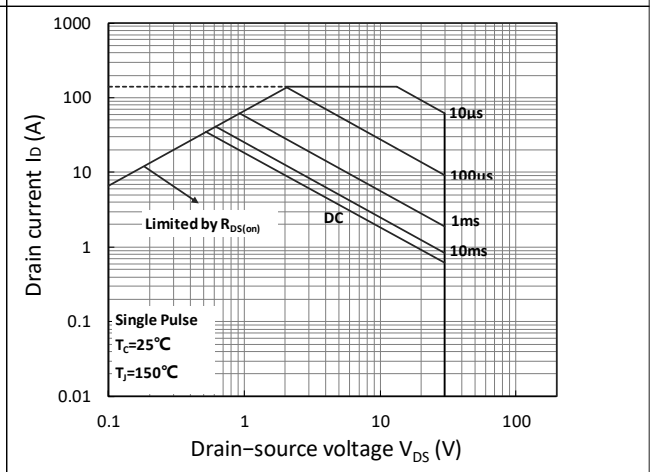


Figure 10. Safe Operating Area

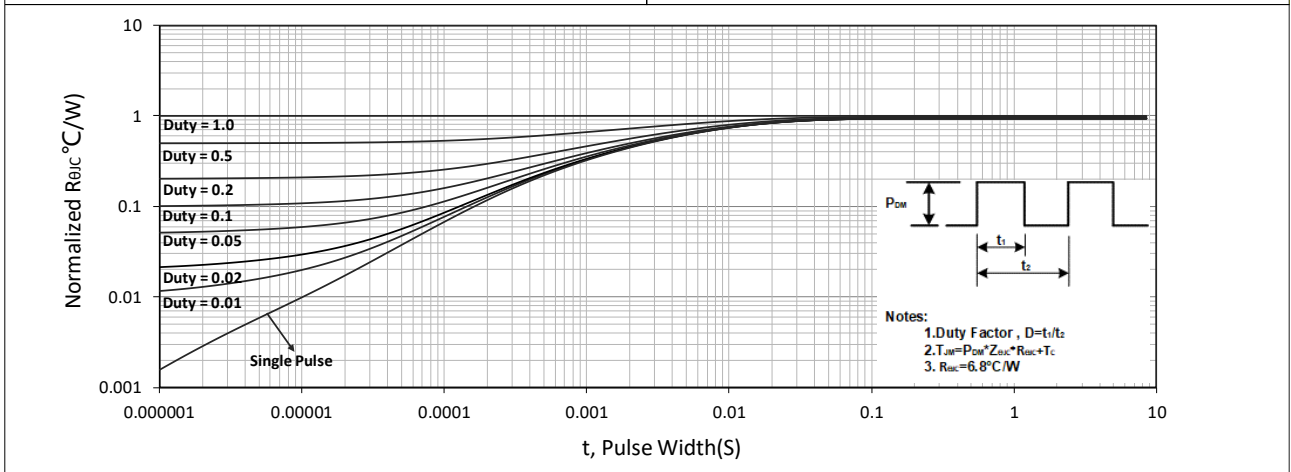


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

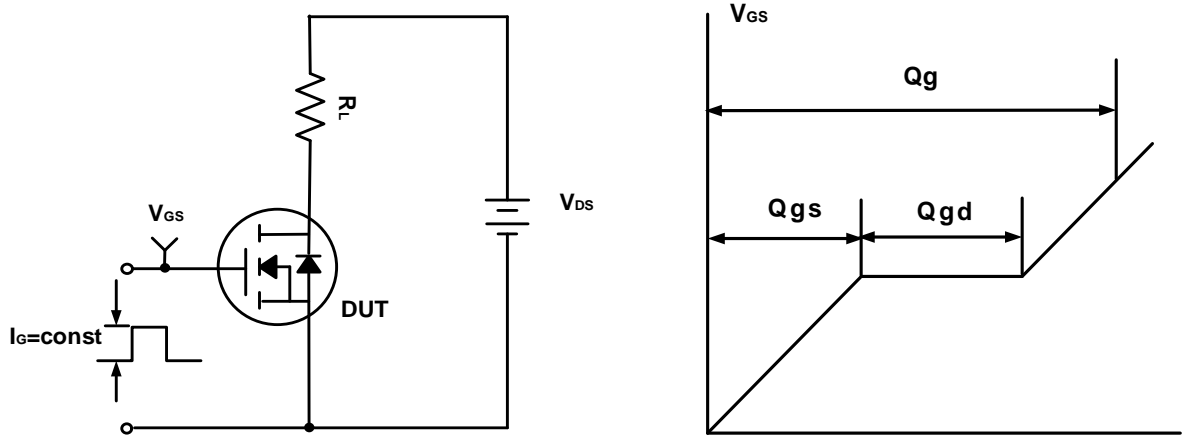


Figure A. Gate Charge Test Circuit & Waveforms

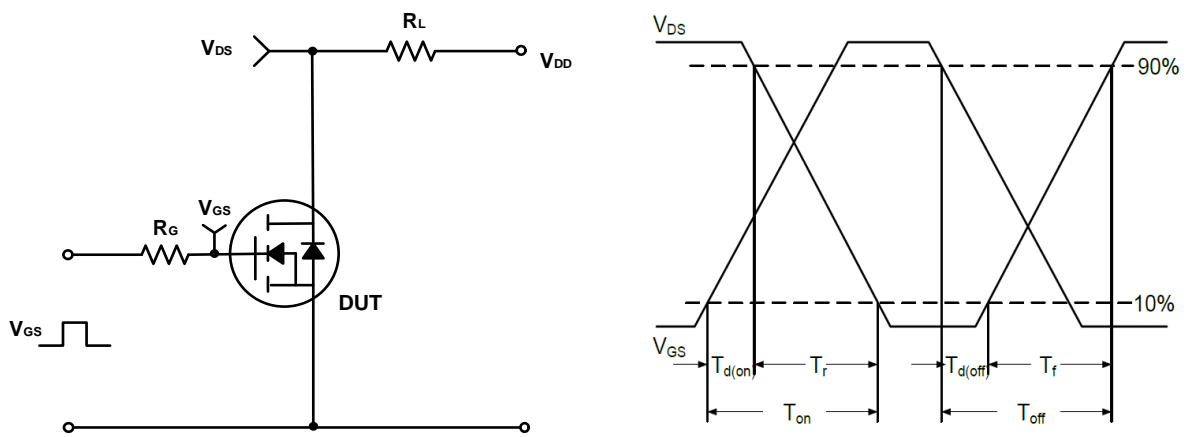


Figure B. Switching Test Circuit & Waveforms

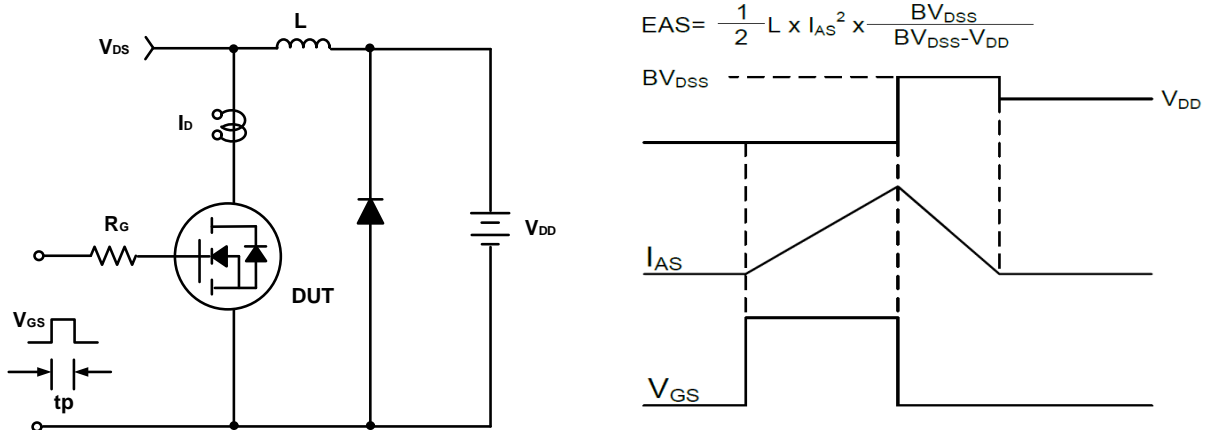
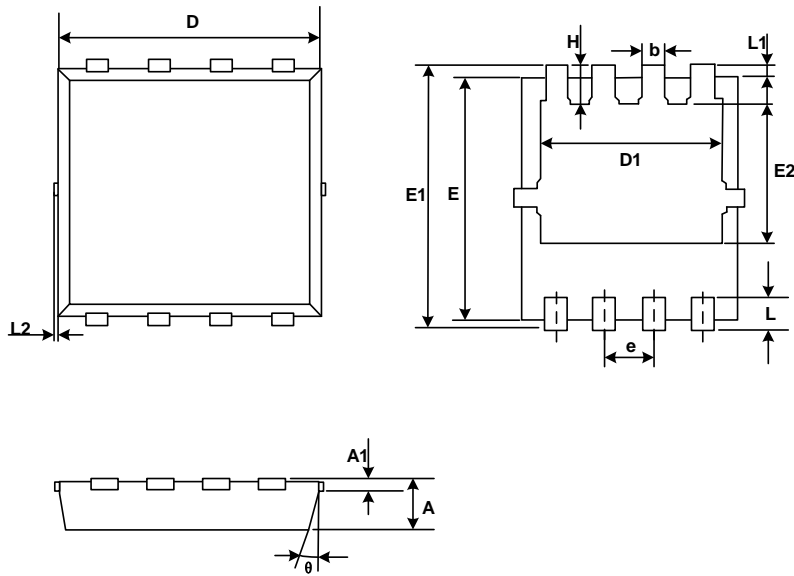


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Mechanical Dimensions for PDFN3030-8L



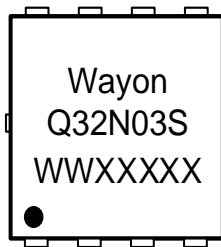
COMMON DIMENSIONS

| SYMBOL | MM | |
|--------|---------|------|
| | MIN | MAX |
| A | 0.65 | 0.90 |
| A1 | 0.10 | 0.25 |
| D | 2.90 | 3.25 |
| D1 | 2.25 | 2.69 |
| E | 2.90 | 3.20 |
| E1 | 3.00 | 3.60 |
| E2 | 1.35 | 2.20 |
| b | 0.20 | 0.40 |
| e | 0.65BSC | |
| L | 0.15 | 0.50 |
| L1 | 0.13BSC | |
| L2 | 0.00 | 0.20 |
| H | 0.15 | 0.65 |
| θ | 0° | 14° |

Ordering Information

| Part | Package | Marking | Packing method |
|------------|-------------|---------|----------------|
| WMQ32N03TS | PDFN3030-8L | Q32N03S | Tape and Reel |

Marking Information



Q32N03S= Device code

WWXXXXX= Date code


Contact Information

No.1001, Shiwan(7) Road, Pudong District, Shanghai, P.R.China.201207

Tel: 86-21-50310888 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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